

Features

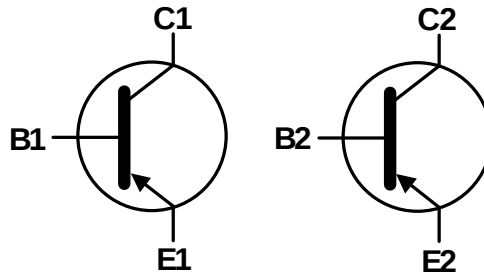
- $BV_{CEO} > -60V$
- $I_{CM} = -1A$ Peak Pulse Current
- General Purpose PNP Transistors Ideally Suited for Low Power Amplification and Switching Applications
- Dual Transistors in a Single SOT26 Package, Taking Half of the Footprint of Two Equivalent Transistors in SOT23
- Epitaxial Planar Die Construction
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

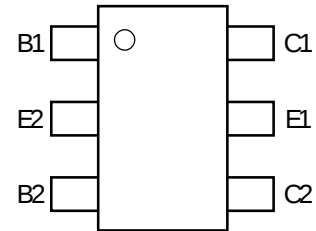
- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.015 grams (Approximate)



Top View



Device Symbol



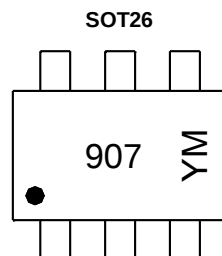
Top View
Pin-Out

Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DMMT2907A-7	AEC-Q101	907	7	8	3,000

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



907 = Product Type Marking Code
YM = Date Code Marking
Y or $\bar{Y}$ = Year (ex: C = 2015)
M or $\bar{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	C	D	E	F	G	H	I	J	K	L	M

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Continuous Collector Current	I _C	-600	mA
Peak Pulsed Collector Current	I _{CM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

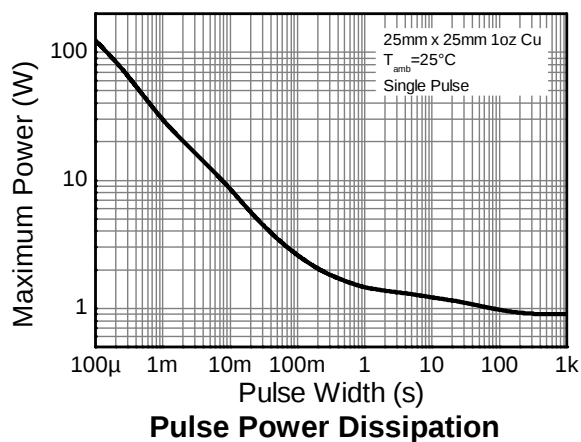
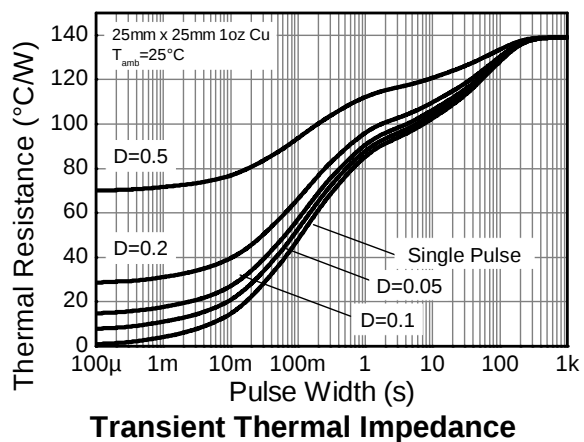
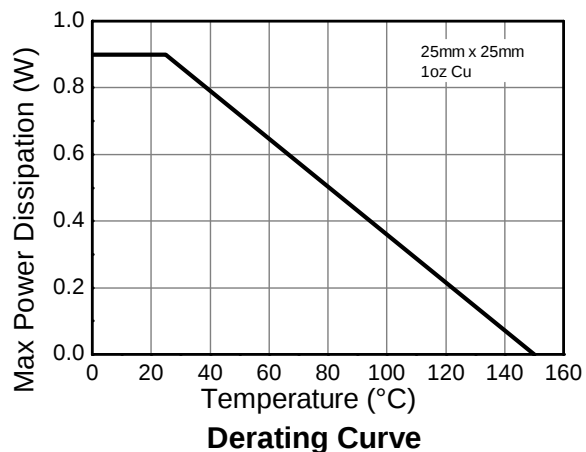
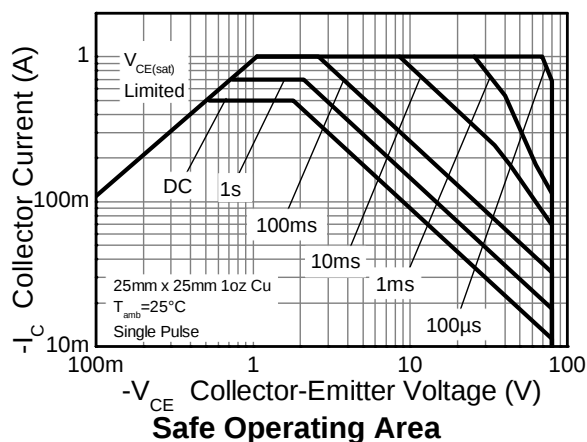
Characteristic	Symbol	Value	Unit
Power Dissipation	P _D	1.28	W
Linear Derating Factor		10.3	
		0.90	mW/°C
		7.14	
Thermal Resistance, Junction to Ambient	R _{θJA}	97	°C/W
		140	
Thermal Resistance, Junction to Lead	R _{θJL}	113	°C
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

- Notes:
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Same as Note 5, except the device is measured at t ≤ 5 seconds.
 7. For a dual device with one active die.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating Information

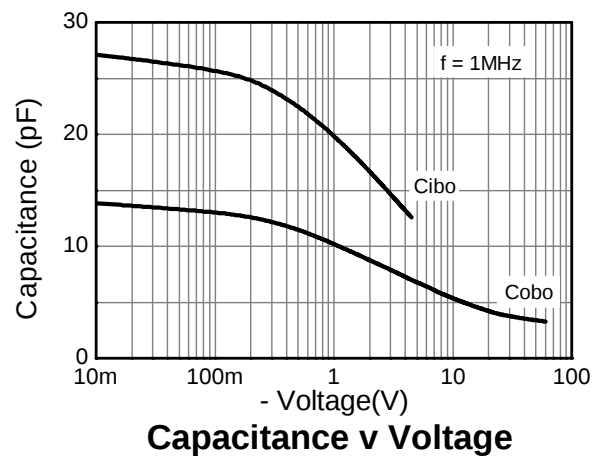
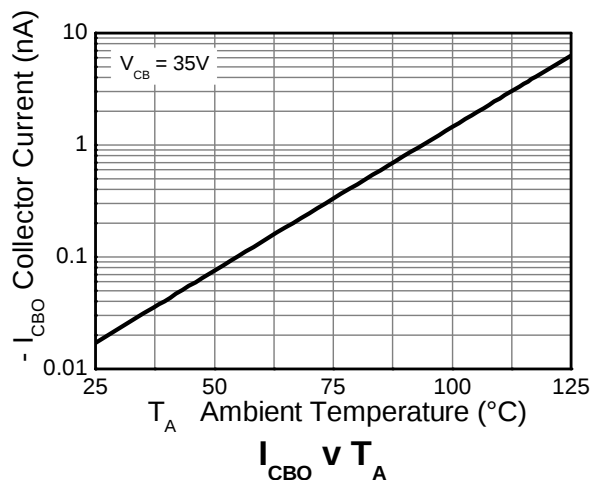
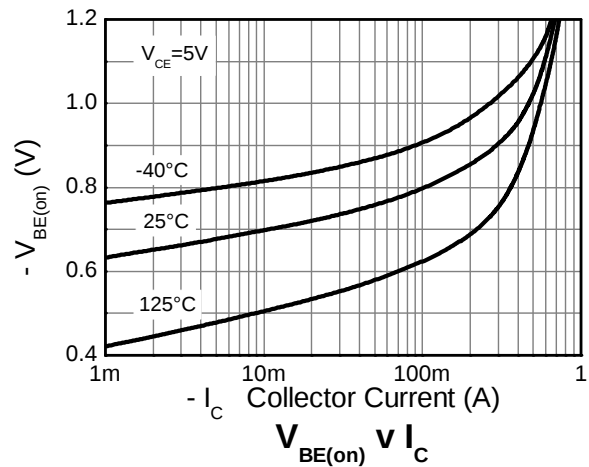
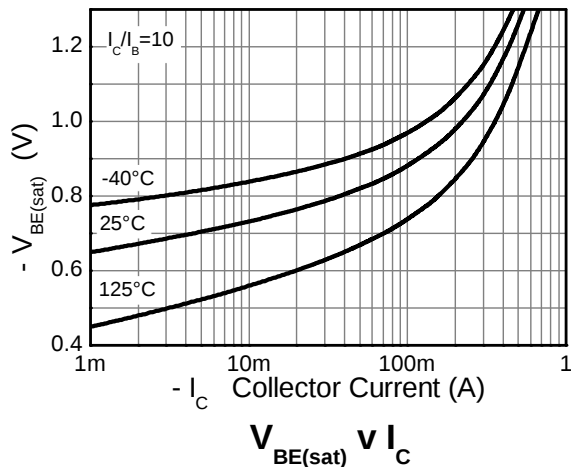
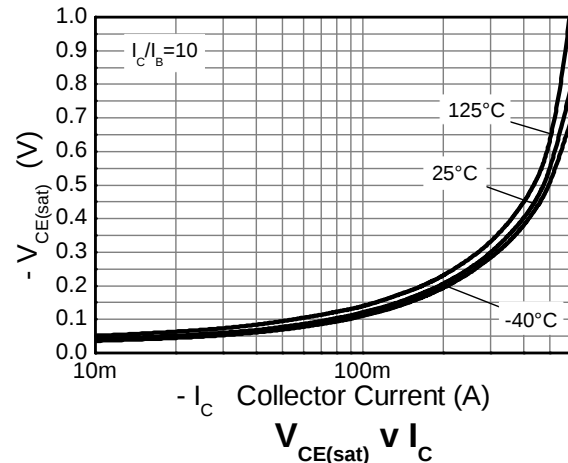
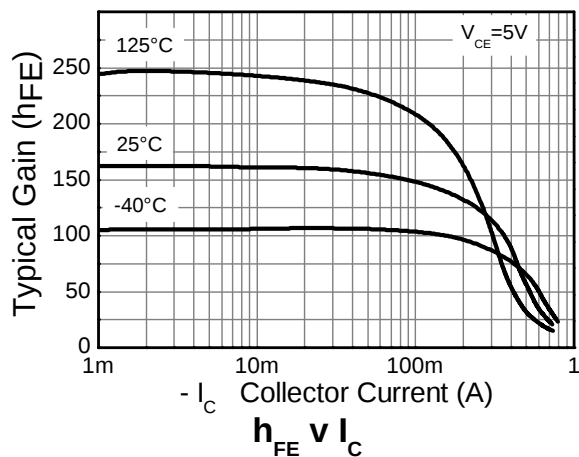


Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV _{CBO}	-60	—	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-60	—	—	V	I _C = -10mA, I _B = 0
Emitter-Base Breakdown Voltage	BV _{EBO}	-5	—	—	V	I _E = -10μA, I _C = 0
Collector-Base Cut-Off Current	I _{CBO}	—	—	-10	nA	V _{CB} = -50V, I _E = 0
		—	—	-10	μA	V _{CB} = -50V, I _E = 0, T _A = +150°C
Collector-Emitter Cut-Off Current	I _{CEV}	—	—	±50	nA	V _{CE} = -30V, V _{BE} = ±0.25V
Base-Emitter Cut-Off Current	I _{BEV}	—	—	±50	nA	V _{CE} = -30V, V _{BE} = ±0.25V
ON CHARACTERISTICS (Note 10)						
DC Current Gain	h _{FE}	75	—	—	—	I _C = -100μA, V _{CE} = -10V
		100	—	—		I _C = -1.0mA, V _{CE} = -10V
		100	—	—		I _C = -10mA, V _{CE} = -10V
		100	—	300		I _C = -150mA, V _{CE} = -10V
		50	—	—		I _C = -500mA, V _{CE} = -10V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	—	—	-0.4	V	I _C = -150mA, I _B = -15mA
		—	—	-1.6		I _C = -500mA, I _B = -50mA
Base-Emitter Saturation Voltage	V _{BE(sat)}	—	—	-1.3	V	I _C = -150mA, I _B = -15mA
		—	—	-2.6		I _C = -500mA, I _B = -50mA
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}	—	5.2	—	pF	V _{CB} = -10V, f = 1.0MHz, I _E = 0mA
Input Capacitance	C _{ibo}	—	16.3	—	pF	V _{EB} = -2.0V, f = 1.0MHz, I _C = 0mA
Current Gain-Bandwidth Product	f _T	200	307	—	MHz	V _{CE} = -2V, I _C = -10mA, f = 100MHz
Turn-On Time	t _{on}	—	—	21	ns	V _{CC} = -30V I _C = -150mA, I _{B1} = -15mA
Delay Time	t _d	—	—	5.5	ns	
Rise Time	t _r	—	—	15.3	ns	
Turn-Off Time	t _{off}	—	—	200	ns	V _{CC} = -6V I _C = -150mA, I _{B1} = I _{B2} = -15mA
Storage Time	t _s	—	—	160	ns	
Fall Time	t _f	—	—	40	ns	

Note: 10. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

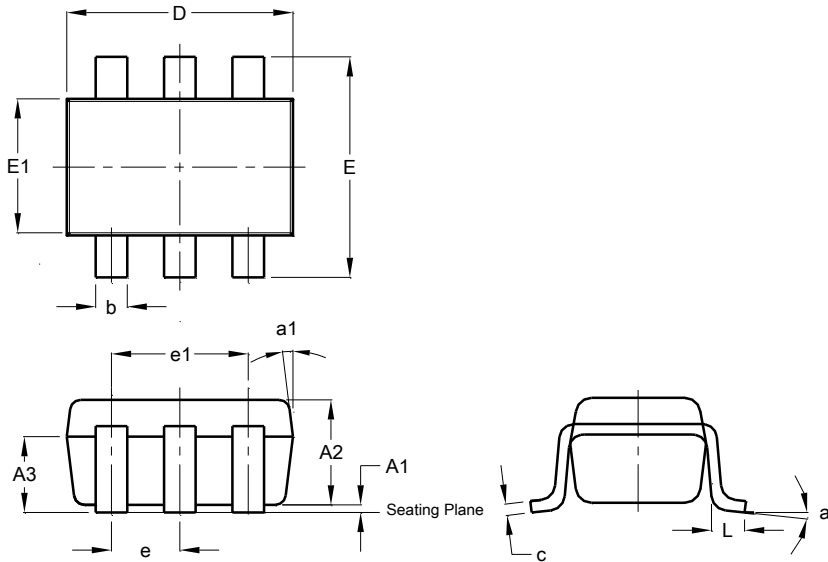
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

SOT26

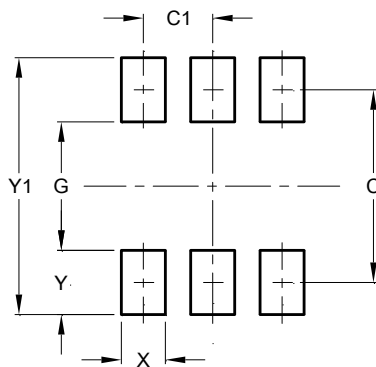


SOT26			
Dim	Min	Max	Typ
A1	0.013	0.10	0.05
A2	1.00	1.30	1.10
A3	0.70	0.80	0.75
b	0.35	0.50	0.38
c	0.10	0.20	0.15
D	2.90	3.10	3.00
e	—	—	0.95
e1	—	—	1.90
E	2.70	3.00	2.80
E1	1.50	1.70	1.60
L	0.35	0.55	0.40
a	—	—	8°
a1	—	—	7°
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

SOT26



Dimensions	Value (in mm)
C	2.40
C1	0.95
G	1.60
X	0.55
Y	0.80
Y1	3.20

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